

# FAST RECOVERY RECTIFIER DIODE

### **MAJOR PRODUCTS CHARACTERISTICS**

I <sub>F(AV)</sub>	3 A
<b>V</b> <sub>RRM</sub>	400 V
t <sub>rr</sub>	25 ns
V <sub>F</sub> (max)	1.4 V

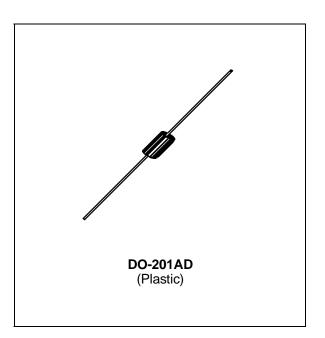
#### **FEATURES**

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING

#### **DESCRIPTION**

Free wheeling diode in converters and motor control circuits.

Rectifiers in S.M.P.S.



## **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit			
V <sub>RRM</sub>	Repetitive peak reverse voltage		400	V		
V <sub>RSM</sub>	Non repetitive peak reverse voltage		400	V		
I <sub>FRM</sub>	Repetive peak forward current	60	Α			
I <sub>F (AV)</sub>	Average forward current*	$T_a = 65$ °C $\delta = 0.5$	3	Α		
IFSM	Surge non repetitive forward current	t <sub>p</sub> = 10ms Sinusoidal	60	Α		
Р	Power dissipation *	T <sub>a=</sub> 65°C	4.2	W		
T <sub>stg</sub> T <sub>j</sub>	Storage and junction temperature range - 40 to + 150 - 40 to + 150					

#### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th (j - a)</sub>	Junction-ambient*	20	C/W

<sup>\*</sup> On infinite heatsink with 10mm lead lengh.

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### STATIC ELECTRICAL CHARACTERISTICS

Synbol	Test	Min.	Тур.	Max.	Unit	
I <sub>R</sub>	T <sub>j</sub> = 25C	$V_R = V_{RRM}$			20	μΑ
	T <sub>j</sub> = 100C				0.5	mA
VF	T <sub>j</sub> = 25C	I <sub>F</sub> = 3A			1.5	V
	T <sub>j</sub> = 100C				1.4	

### **RECOVERY CHARACTERISTICS**

S	Symbol	Test Conditions			Тур.	Max.	Unit
	t <sub>rr</sub>	$T_j = 25C$	$I_F = 1A$ $di_F/dt = -15A/\mu s$ $V_R = 30V$			55	ns
			IF = 0.5A IR = 1 A Irr = 0.25A			25	

### TURN-OFF SWITCHING CHARACTERISTICS - Without series inductance

Symbol	Tes	Min.	Тур.	Max.	Unit		
t <sub>IRM</sub>	dir/dt = - 50A/μs	Vcc = 200 V	IF = 3A		35	50	ns
I <sub>RM</sub>	di <sub>F</sub> /dt = -50A/μs	L <sub>p</sub> ≤ 0.05μH	$T_j = 100^{\circ}C$		1.5	2	Α

To evaluate the conduction losse use the following equations :  $V_F = 1.1 + 0.050~I_F$   $P = 1.1~x~I_{F(AV)} + 0.050~I_F^2_{(RMS)}$ 

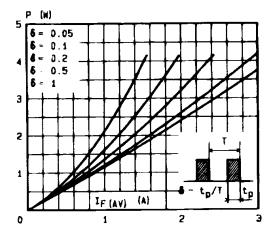


Fig.1 - Maximum average power dissipation versus average forward current.

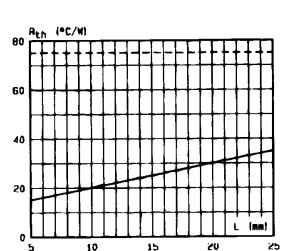


Fig.3 Thermal resistance versus lead length.

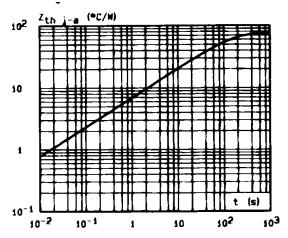


Fig.4 - Transient thermal impedance junction-ambient for mounting  $n^2$ 2 versus pulse duration (L = 10 mm).

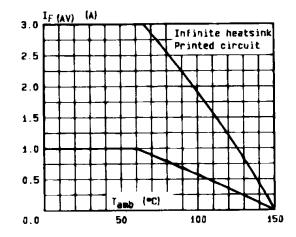
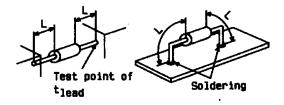


Fig.2 - Average forward current versus ambient temperature.

Mounting nºi Mo INFINITE HEATSINK PR

Mounting n°2 PRINTED CIRCUIT



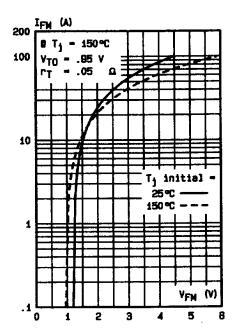


Fig.5 - Peak forward current versus peak forward voltage drop (maximum values).

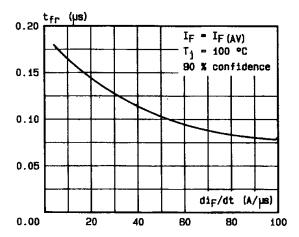


Fig.7 - Recovery time versus  $di_F/dt$ .

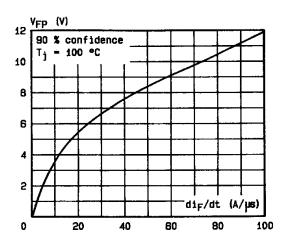


Fig.8 - Peak forward voltage versus dip/dt.

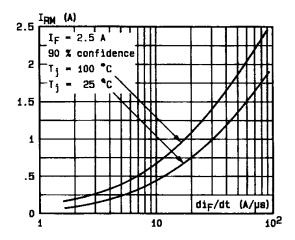


Fig.9 - Peak reverse current versus  $\mathrm{di}_{\mathrm{F}}/\mathrm{dt}$ .

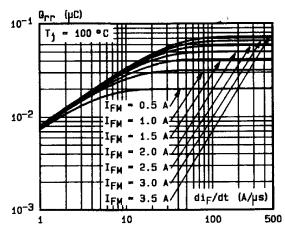


Fig.10  $\sim$  Recovered charge versus  $di_F/dt$  (typical values).

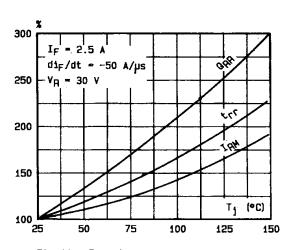


Fig.11 - Dynamic parameters versus junction temperature.

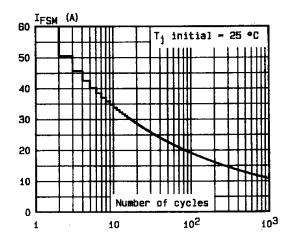
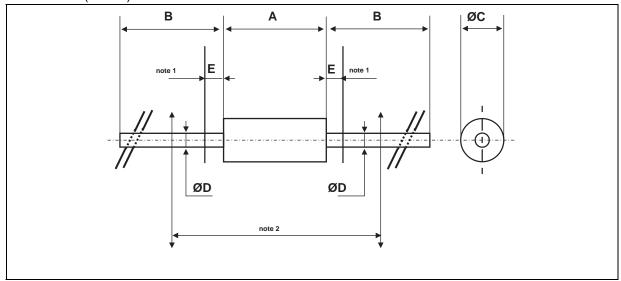


Fig.12 - Non repetitive surge peak current versus number of cycles

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#### **PACKAGE MECHANICAL DATA**

DO-201AD (Plastic)



		DIMEN	ISIONS					
REF.	Millimeters		Inches		NOTES			
	Min.	Max.	Min.	Max.				
Α		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E			
В	25.40		1.000		2 - The minimum axial lengh within which the device may be			
ØC		5.30		0.209	placed with its leads bent at right angles is 0.59"(15 mm)			
Ø D		1.30		0.051				
Е		1.25		0.049				

- Marking: type number, white band indicate cathode
- Cooling method: by convection (method A)
- Weight: 1g

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